

Application No. 09/440,928

Attorney Docket 040301/0578

**CLAIM AMENDMENTS FOR EXAMINER'S AMENDMENT**

23. (Currently Amended) A semiconductor device comprising:

an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film formed on the channel forming region, and a gate electrode formed on the insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the insulating gate film [[via]] over and in contact with the first region, the first and second regions having an identical conductivity type;

an elevated electrode formed on the main electrodes, and having a third region including a third group IV element and a fourth group IV element and a fourth region formed on the main electrode [[via]] over and in contact with the third region and including the third group IV element;

a first silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element; and

a second silicide electrode formed in contact with the fourth region of the elevated electrode, and being substantially free from the fourth group IV element.

32. (Currently Amended) A semiconductor device comprising:

a first conductivity type insulated gate field effect transistor having a pair of first conductivity type main electrodes used as source and drain electrodes, a second conductivity type channel forming region provided between the pair of first conductivity type main electrodes, a first insulating gate film formed on the second conductivity type channel forming region, and a first gate electrode formed on the first insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the first insulating gate film, and a second region including the first group IV element and formed on the first insulating gate film [[via]] over and in contact with the first region, the first and second regions having an identical conductivity type; and

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**CLAIM AMENDMENTS FOR EXAMINER'S AMENDMENT (cont'd)**

a second conductivity type insulated gate field effect transistor having a pair of second conductivity type main electrodes used as source and drain electrodes, a first conductivity type channel forming region provided between the pair of second conductivity type main electrodes, a second insulating gate film formed on the first conductivity type channel forming region, and a second gate electrode formed on the second insulating gate film, and provided with a third region including the first group IV element and the second group IV element and formed in contact with the second insulating gate film, and a fourth region including the first group IV element and formed on the second insulating gate film [[via]] over and in contact with the third region, the third and fourth regions having the identical conductivity type.